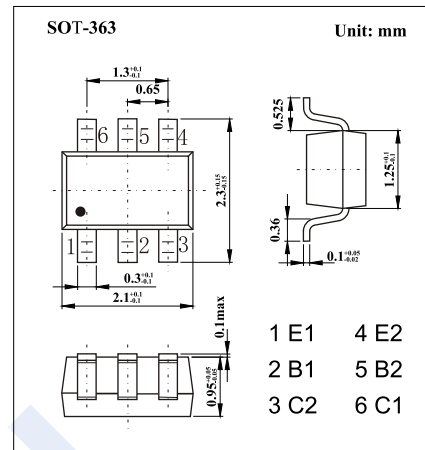


PNP Transistors

MMDT5401 (KMDT5401)

■ Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Dual Transistors (PNP+PNP)
- Complementary NPN Type Available(MMDT 5551)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-160	V
Collector - Emitter Voltage	V _{CEO}	-150	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-0.2	A
Collector Power Dissipation	P _C	0.2	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-160			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B =0	-150			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -120 V, I _E =0			-0.05	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -4V, I _C =0			-0.05	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10 mA, I _B =-1mA			-0.2	V
		I _C =-50 mA, I _B =-5mA			-0.5	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-10 mA, I _B =-1mA			-1	
		I _C =-50 mA, I _B =-5mA			-1	
DC current gain	h _{FE(1)}	V _{CE} = -5V, I _C = -1mA	50			
	h _{FE(2)}	V _{CE} = -5V, I _C = -10mA	100		300	
	h _{FE(3)}	V _{CE} = -5V, I _C = -50mA	50			
Noise Figure	NF	V _{CE} = -5.0V, I _C = -200μA, R _S = 10Ω, f = 1kHz			8	dB
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz			6	pF
Transition frequency	f _T	V _{CE} = -10V, I _C = -10mA, f=100MHz	100			MHz

■ Marking

Marking	K4M
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